

Ordering number : ENN6937

P-Channel Silicon MOSFET



**CPH6352**

**Ultrahigh-Speed Switching Applications**

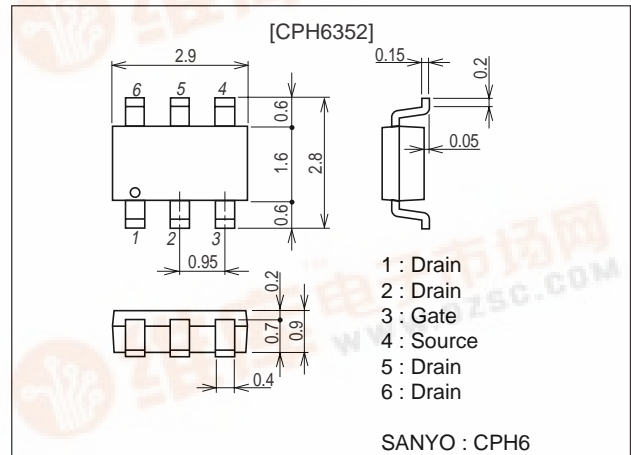
**Features**

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

**Package Dimensions**

unit : mm

2151A



**Specifications**

**Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		-3	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-12	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm²X0.8mm)	1.6	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0	-30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0			-10	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-0.4		-1.4	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1.5A	3	4.4		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-1.5A, V <sub>GS</sub> =-4V		120	160	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-0.5A, V <sub>GS</sub> =-2.5V		170	240	mΩ

Marking : JF

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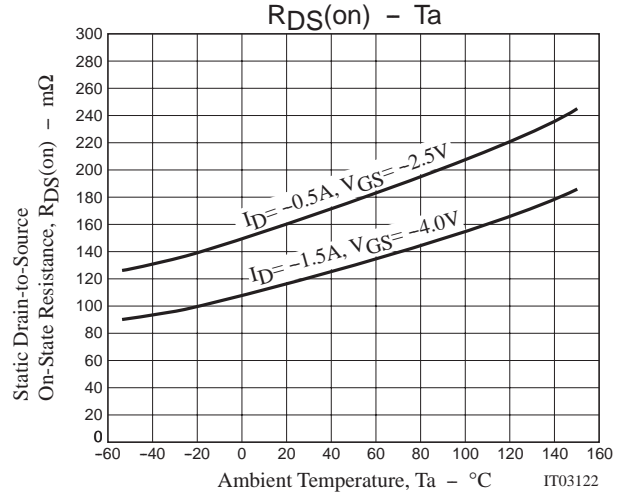
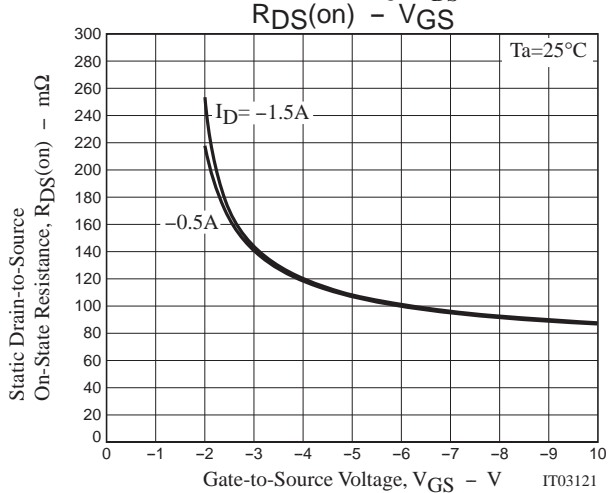
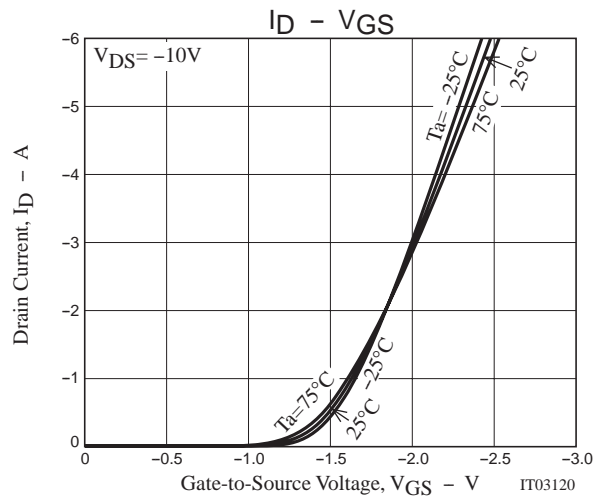
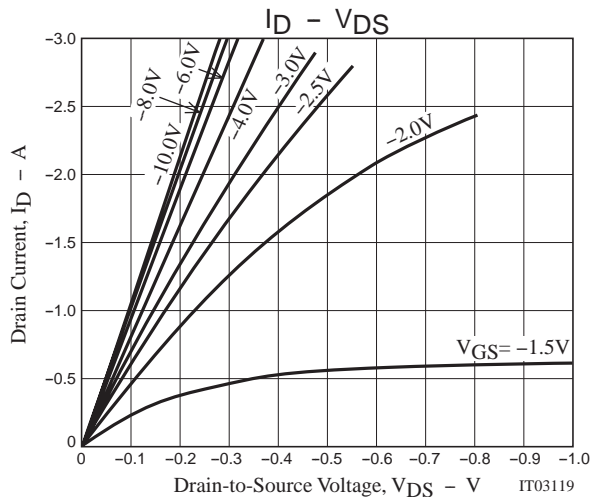
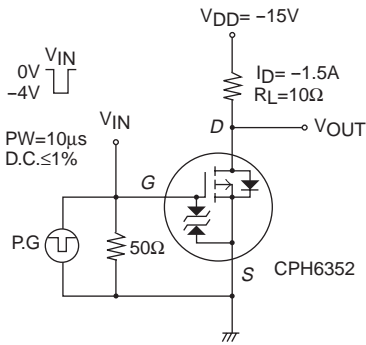


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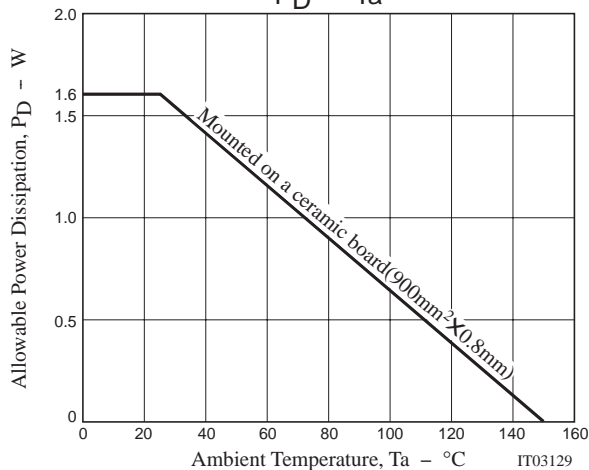
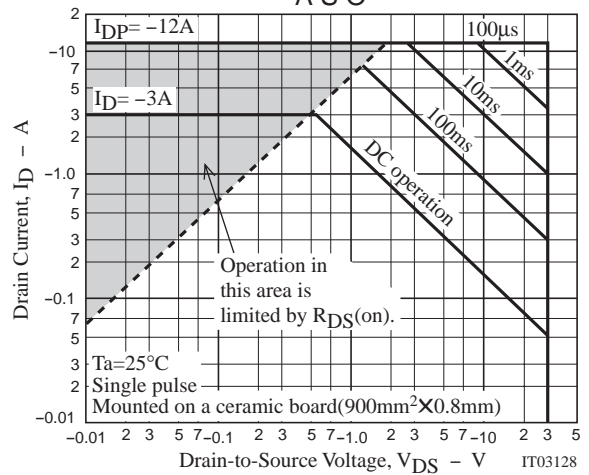
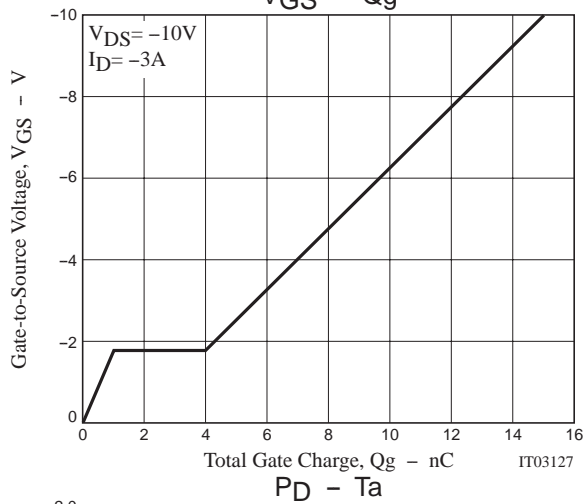
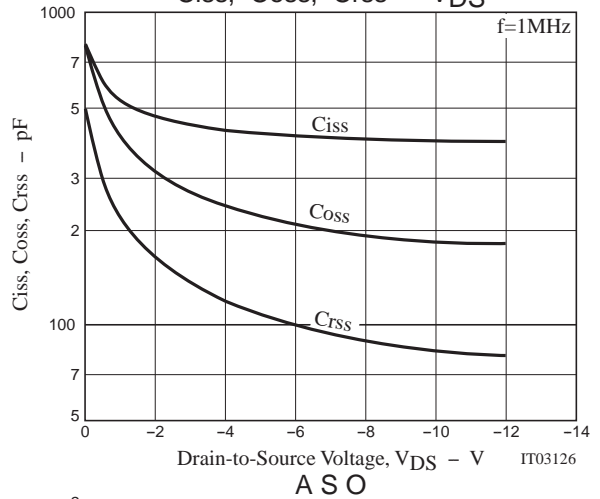
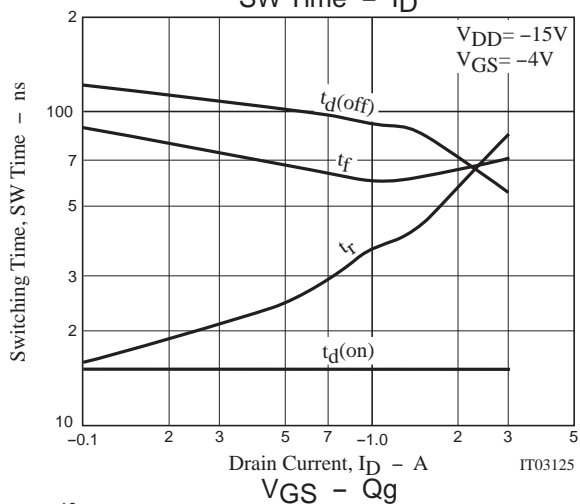
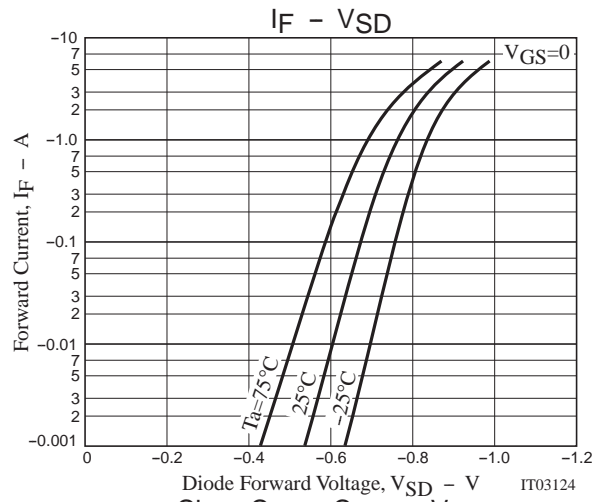
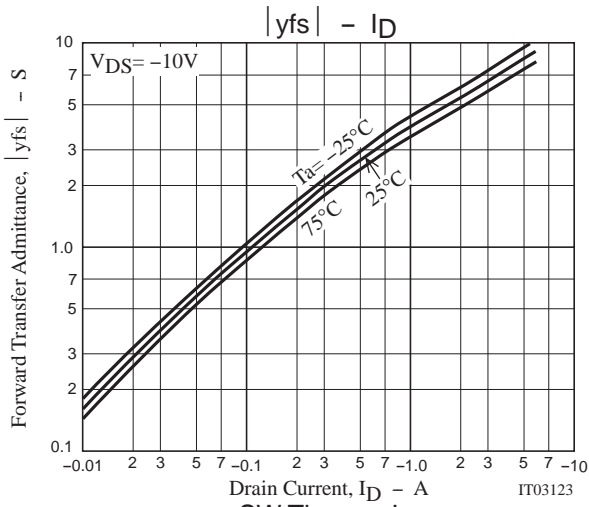
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V <sub>DS</sub> =-10V, f=1MHz		380		pF
Output Capacitance	Coss	V <sub>DS</sub> =-10V, f=1MHz		180		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =-10V, f=1MHz		80		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit		15		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit		45		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit		85		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit		62		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A		15		nC
Gate-to-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A		1		nC
Gate-to-Drain "Miller" Charge	Q <sub>gd</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A		3		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-3A, V <sub>GS</sub> =0		-0.85	-1.5	V

## Switching Time Test Circuit



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